ADC1010S series

Single 10-bit ADC; 65 Msps, 80 Msps, 105 Msps or 125 Msps; CMOS or LVDS DDR digital outputs

Rev. 01 — 9 April 2010

Preliminary data sheet

1. General description

The ADC1010S is a single-channel 10-bit Analog-to-Digital Converter (ADC) optimized for high dynamic performances and low power consumption at sample rates up to 125 Msps. Pipelined architecture and output error correction ensure the ADC1010S is accurate enough to guarantee zero missing codes over the entire operating range. Supplied from a single 3 V source, it can handle output logic levels from 1.8 V to 3.3 V in CMOS mode, thanks to a separate digital output supply. It supports the LVDS (Low Voltage Differential Signalling) DDR (Double Data Rate) output standard. An integrated SPI (Serial Peripheral Interface) allows the user to easily configure the ADC. The device also includes a SPI programmable full-scale to allow flexible input voltage range from 1 V to 2 V (peak-to-peak). With excellent dynamic performance from the baseband to input frequencies of 170 MHz or more, the ADC1010S is ideal for use in communications, imaging and medical applications.

2. Features and benefits

- SNR, 62 dBFS; SFDR, 86 dBc
- Sample rate up to 125 Msps
- 10-bit pipelined ADC core
- Clock input divider by 2 for less jitter contribution
- Single 3 V supply
- Flexible input voltage range: 1 V p-p to 2 V p-p
- CMOS or LVDS DDR digital outputs
- Pin compatible with the ADC1410S series and the ADC1210S series
- HVQFN40 package

- Input bandwidth, 600 MHz
- Power dissipation, 430 mW at 80 Msps
- Serial Peripheral Interface (SPI)
- Duty cycle stabilizer
- Fast OuT of Range (OTR) detection
- INL ±0.07 LSB, DNL ±0.04 LSB
- Offset binary, two's complement, gray
- Power-down and Sleep modes

3. Applications

- Wireless and wired broadband communications
- Spectral analysis
- Ultrasound equipment

- Portable instrumentation
- Imaging systems
- Software define radio

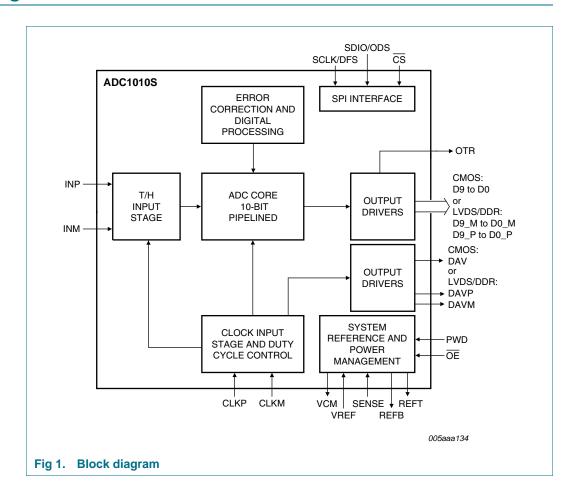


4. Ordering information

Table 1. Ordering information

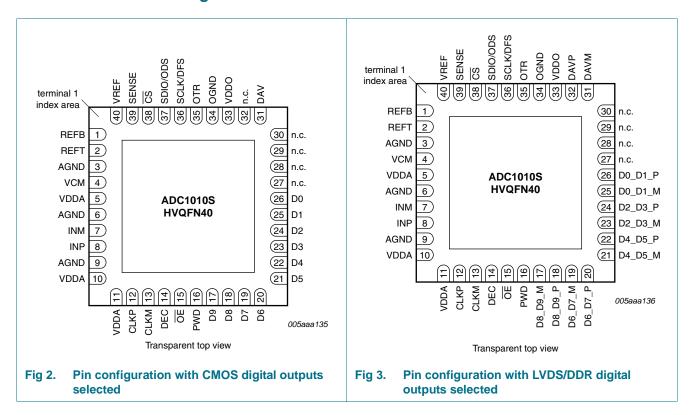
Type number	f _s (Msps)	Package		
		Name	Description	Version
ADC1010S125HN/C1	125	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6\times6\times0.85$ mm	SOT618-6
ADC1010S105HN/C1	105	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6\times6\times0.85$ mm	SOT618-6
ADC1010S080HN/C1	80	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6\times6\times0.85$ mm	SOT618-6
ADC1010S065HN/C1	65	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6\times6\times0.85$ mm	SOT618-6

5. Block diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description (CMOS digital outputs)

			0 1 ,
Symbol	Pin	Type 11	Description
REFB	1	0	bottom reference
REFT	2	0	top reference
AGND	3	G	analog ground
VCM	4	0	common-mode output voltage
VDDA	5	Р	analog power supply
AGND	6	G	analog ground
INM	7	I	complementary analog input
INP	8	I	analog input
AGND	9	G	analog ground
VDDA	10	Р	analog power supply
VDDA	11	Р	analog power supply
CLKP	12	I	clock input
CLKM	13	I	complementary clock input
DEC	14	0	regulator decoupling node
ŌE	15	1	output enable, active LOW
PWD	16	I	power down, active HIGH

 Table 2.
 Pin description (CMOS digital outputs) ...continued

Symbol	Pin	Type ^[1]	Description
D9	17	Ο	data output bit 9 (MSB)
D8	18	0	data output bit 8
D7	19	0	data output bit 7
D6	20	0	data output bit 6
D5	21	0	data output bit 5
D4	22	0	data output bit 4
D3	23	0	data output bit 3
D2	24	0	data output bit 2
D1	25	0	data output bit 1
D0	26	0	data output bit 0 (LSB)
n.c.	27	-	not connected
n.c.	28	-	not connected
n.c.	29	-	not connected
n.c.	30	-	not connected
DAV	31	0	data valid output clock
n.c.	32	-	not connected
VDDO	33	Р	output power supply
OGND	34	G	output ground
OTR	35	0	out of range
SCLK/DFS	36	I	SPI clock
			data format select
SDIO/ODS	37	I/O	SPI data IO
			output data standard
CS	38	I	SPI chip select
SENSE	39	I	reference programming pin
VREF	40	I/O	voltage reference input/output

^[1] P: power supply; G: ground; I: input; O: output; I/O: input/output.

Table 3. Pin description (LVDS/DDR) digital outputs)

Symbol	Pin[1]	Type[2]	Description
D8_D9_M	17	0	differential output data D8 and D9 multiplexed, complement
D8_D9_P	18	0	differential output data D8 and D9 multiplexed, true
D6_D7_M	19	0	differential output data D6 and D7 multiplexed, complement
D6_D7_P	20	0	differential output data D6 and D7 multiplexed, true
D4_D5_M	21	0	differential output data D4 and D5 multiplexed, complement
D4_D5_P	22	0	differential output data D4 and D5 multiplexed, true
D2_D3_M	23	0	differential output data D2 and D3 multiplexed, complement
D2_D3_P	24	0	differential output data D2 and D3 multiplexed, true
D0_D1_M	25	0	differential output data D0 and D1 multiplexed, complement
D0_D1_P	26	0	differential output data D0 and D1 multiplexed, true
n.c.	27	-	not connected
n.c.	28	-	not connected
n.c.	29	-	not connected

Table 3. Pin description (LVDS/DDR) digital outputs) ...continued

Symbol	Pin ^[1]	Type ^[2]	Description
n.c.	30	-	not connected
DAVM	31	0	data valid output clock, complement
DAVP	32	0	data valid output clock, true

^[1] Pins 1 to 16 and pins 33 to 40 are the same for both CMOS and LVDS DDR outputs (see Table 2)

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Vo	output voltage	pins D9 to D0 or pins D9P to D0P and D9M to D0M	-0.4	+3.9	V
V_{DDA}	analog supply voltage		-0.4	+3.9	V
V_{DDO}	output supply voltage		-0.4	+3.9	V
T _{stg}	storage temperature		–55	+125	°C
T _{amb}	ambient temperature		-40	+85	°C
Tj	junction temperature		-	125	°C

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	22.5	K/W
R _{th(j-c)}	thermal resistance from junction to case		[1]	11.7	K/W

^[1] Value for six layers board in still air with a minimum of 25 thermal vias

^[2] P: power supply; G: ground; I: input; O: output; I/O: input/output.

9. Static characteristics

Table 6. Static characteristics[1]

Supplies VDDA analog supply voltage CMOS mode 1.65 1.8 3.6 V VDDO output supply voltage CMOS mode 1.65 1.8 3.6 V IDDA analog supply current f _{clk} = 125 Msps; f₁=70 MHz - 210 - mA IDDO output supply current CMOS mode; f _{clk} = 125 Msps; f₁=70 MHz - 210 - mA IDDO output supply current CMOS mode; f _{clk} = 125 Msps; f₁=70 MHz - 210 - mA P power dissipation ADC1010S105; analog supply only - 630 - mW ADC1010S105; analog supply only - 430 - mW ADC1010S080; analog supply only - 430 - mW ADC1010S081 - 36 - mW Viget/add differential clock input voltage peak-to-peak - ±1.6 ∨ V Viget/add differential clock input voltage peak-to-peak ±0.7	Table 6.	Static characteristics					
VDDA analog supply voltage CMOS mode 1.65 1.8 3.6 V VDDO output supply voltage EMOS mode 1.65 1.8 3.6 V IDDA analog supply current f _{clk} = 125 Msps; f₁ =70 MHz - 2.0 - mA IDDO output supply current CMOS mode; f _{clk} = 125 Msps; f₁ =70 MHz - 10 - mA IDDD power dissipation ADC1010S105; analog supply only - 630 - mW ADC1010S105; analog supply only - 430 - mW ADC1010S080; analog supply only - 430 - mW ADC1010S080; analog supply only - 430 - mW ADC1010S080; analog supply only - 430 - mW ADC1010S105 - 430 - mW ADC1010S106; analog supply only - 40 - mW EVENDES - - 40 - mW Stription of	Symbol	Parameter	Conditions	Min	Тур	Max	Uni
VDDDO	Supplies						
LVDS DDR mode		• • • • • • • • • • • • • • • • • • • •					
DDDA	V_{DDO}	output supply voltage		1.65	1.8	3.6	V
Debo			LVDS DDR mode	2.85	3.0	3.6	V
	I _{DDA}	analog supply current		-	210	-	mΑ
Pack Power dissipation ADC1010S125; analog supply only ADC1010S125; analog supply only ADC1010S105; analog supply only ADC1010S080; analog supply only ADC1010S0800; analog supply only ADC1010S0800; analog supply only ADC1010S0805; analog supply only ADC1010S0805; analog supply only ADC1010S065; analog supply only analog supply only analog supply only analog supply only ADC1010S065; analog supply only analog supply only ADC1010S065; analog supply only analog supply only analog supply only ADC1010S065; analog supply only analog supply only analog supply only ADC1010S065; analog supply only analog supply only ADC1010S065; analog supply only ADC1010S065; analog supply only ADC1010S065; analog supply only analog supply o	I _{DDO}	output supply current	•	-	10	-	mA
ADC1010S105; analog supply only ADC1010S105; analog supply only ADC1010S080; analog supply only Dewer-down mode 3 3 3 3 7 mW MW MW MW MW MW MW MW				-	35	-	mΑ
ADC1010S080; analog supply only ADC1010S080; analog supply only ADC1010S080; analog supply only ADC1010S065; analog supply only ADC1010S065; analog supply only Dever-down mode Reprint	Р	power dissipation	•	-	630	-	mW
ADC1010S065; analog supply only ADC1010S065; analog supply only ADC1010S065; analog supply only Power-down mode 2 2 7 MW MW MW MW MW MW MW			•	-	550	-	mW
Parison Pari			•	-	430	-	mW
Seleep mode			•	-	380	-	mW
Clock inputs: pins CLKP and CLKM			power-down mode	-	2	-	mW
LVPECL V _{(clk)dif} differential clock input voltage peak-to-peak - ±1.6 - V LVDS V _{(clk)dif} differential clock input voltage peak-to-peak - ±0.70 - V SINE wave V _{(clk)dif} differential clock input voltage peak-to-peak ±0.8 ±3.0 - V LV (clk)dif differential clock input voltage peak-to-peak ±0.8 ±3.0 - V LV (clk)dif ±0.8 ±3.0 - V LV (clk)dif differential clock input voltage peak-to-peak ±0.8 ±3.0 - V LV (clk)dif differential clock input voltage 0.3V (blk) V LV (LVCMOS) LV (blg) LV (blg) LV (blg) LV (blg) V LV (blg) LV (blg) V LV (blg) LV (blg) V </td <td></td> <td></td> <td>sleep mode</td> <td>-</td> <td>40</td> <td>-</td> <td>mW</td>			sleep mode	-	40	-	mW
Vicolkydif differential clock input voltage peak-to-peak - ±1.6 - V V V V V V V V V	Clock inp	uts: pins CLKP and CLKM					
Vicinity of the total clock input voltage peak-to-peak peak	LVPECL						
Vi(clk)dif differential clock input voltage peak-to-peak - ±0.70 - V SINE wave Vi(clk)dif differential clock input voltage peak-to-peak ±0.8 ±3.0 - V LVCMOOS VIL LOW-level input voltage - - 0.3V _{DDA} V VIH HIG-level input voltage - 0.7V _{DDA} - V Logic inputs: pins PWD and OE VIL LOW-level input voltage 0 - 0.8 V VIL LOW-level input voltage 2 - V _{DDA} V IIL LOW-level input current - <t< td=""><td>$V_{i(clk)dif}$</td><td>differential clock input voltage</td><td>peak-to-peak</td><td>-</td><td>±1.6</td><td>-</td><td>V</td></t<>	$V_{i(clk)dif}$	differential clock input voltage	peak-to-peak	-	±1.6	-	V
SINE wave SINE	LVDS						
V _{I(CIk)dif} differential clock input voltage peak-to-peak ±0.8 ±3.0 - V LVCMOS VI _{IL} LOW-level input voltage - - 0.3V _{DDA} V V _{IH} HIG-level input voltage 0.7V _{DDA} - - V V _{IL} LOW-level input voltage 0 - 0.8 V V _{IH} HIGH-level input voltage 2 - V _{DDA} V I _{IL} LOW-level input current -10 - +10 μA Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS V _{IL} LOW-level input voltage 0 - 0.3V _{DDA} V V _I HIGH-level input voltage 0.7V _{DDA} - V _{DDA} V I _{IL} LOW-level input current -10 - +10 μA I _{IL} LOW-level input current -7 +50 μA	$V_{i(clk)dif}$	differential clock input voltage	peak-to-peak	_	±0.70	-	V
LVCMOS V _{IL} LOW-level input voltage - - 0.3V _{DDA} V V _{IH} HIG-level input voltage 0.7V _{DDA} - - V Logic inputs: pins PWD and OE V LOW-level input voltage 0 - 0.8 V V _{IL} LOW-level input voltage 2 - V _{DDA} V I _{IL} LOW-level input current - <td>SINE wave</td> <td>9</td> <td></td> <td></td> <td></td> <td></td> <td></td>	SINE wave	9					
VIH HIG-level input voltage 0.7V _{DDA} - - V Logic inputs: pins PWD and OE V L V D A V V V D A V D A V D D A D D A D <td></td> <td>differential clock input voltage</td> <td>peak-to-peak</td> <td>±0.8</td> <td>±3.0</td> <td>-</td> <td>V</td>		differential clock input voltage	peak-to-peak	±0.8	±3.0	-	V
	V _{IL}	LOW-level input voltage		-	-	$0.3V_{DDA}$	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{IH}	HIG-level input voltage		$0.7V_{DDA}$	-	-	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Logic inp	uts: pins PWD and OE					
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{IL}	LOW-level input voltage		0	-	0.8	V
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		HIGH-level input voltage		2	-	V_{DDA}	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		LOW-level input current		<tbd></tbd>	-	<tbd></tbd>	μΑ
$ V_{IL} \qquad LOW-level input voltage \qquad \qquad 0 \qquad - \qquad 0.3V_{DDA} V \\ V_{IH} \qquad HIGH-level input voltage \qquad \qquad 0.7V_{DDA} - \qquad V_{DDA} V \\ I_{IL} \qquad LOW-level input current \qquad \qquad -10 \qquad - \qquad +10 \qquad \mu A \\ I_{IH} \qquad HIGH-level input current \qquad \qquad -50 \qquad - \qquad +50 \qquad \mu A $	I _{IH}	HIGH-level input current		-10	-	+10	μΑ
V_{IH} HIGH-level input voltage 0.7 V_{DDA} - V_{DDA} V I_{IL} LOW-level input current -10 - +10 μA I_{IH} HIGH-level input current -50 - +50 μA	Serial per	ipheral interface: pins CS, SDIO/OD	OS, SCLK/DFS				
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V _{IL}	LOW-level input voltage		0	-	$0.3V_{DDA}$	V
I_{IL} LOW-level input current -10 - $+10$ μA I_{IH} HIGH-level input current -50 - $+50$ μA	V _{IH}	HIGH-level input voltage		0.7V _{DDA}	-		
I_{IH} HIGH-level input current -50 - $+50$ μA		LOW-level input current			-	+10	μΑ
		HIGH-level input current		-50	-	+50	μΑ
	Cı	input capacitance		-	4	-	

 Table 6.
 Static characteristics
 [1]
 ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Digital ou	tputs, CMOS mode: pins D9 to D0	, OTR, DAV				
Output lev	rels, V _{DDO} = 3 V					
V _{OL}	LOW-level output voltage	$I_{OL} = \langle tbd \rangle$	OGND	-	$0.2V_{DDO}$	V
V _{OH}	HIGH-level output voltage	$I_{OH} = \langle tbd \rangle$	$0.8V_{DDO}$	-	V_{DDO}	V
I _{OL}	LOW-level output current	3-state; output level = 0 V	-	<tbd></tbd>	-	μΑ
I _{OH}	HIGH-level output current	3-state; output level = V _{DDA}	-	<tbd></tbd>	-	μΑ
Co	output capacitance	high impedance; \overline{OE} = HIGH	-	3	-	pF
Output lev	rels, V _{DDO} = 1.8 V					
V _{OL}	LOW-level output voltage	$I_{OL} = \langle tbd \rangle$	OGND	-	$0.2V_{DDO}$	٧
V _{OH}	HIGH-level output voltage	$I_{OH} = \langle tbd \rangle$	$0.8V_{DDO}$	-	V_{DDO}	٧
Digital ou	tputs, LVDS mode: pins D9P to D0	P, D9M to D0M, DAVP and DAVM				
Output lev	rels, $V_{DDO} = 3 \text{ V}$ only, $R_L = 100 \Omega$					
$V_{O(offset)}$	output offset voltage	output buffer current set to 3.5 mA	-	1.2	-	V
$V_{O(dif)}$	differential output voltage	output buffer current set to 3.5 mA	-	350	-	mV
Co	output capacitance		-	<tbd></tbd>	-	pF
Analog in	puts: pins INP and INM					
l _l	input current		-5	-	+5	μΑ
R _I	input resistance		-	<tbd></tbd>	-	Ω
Cı	input capacitance		-	5	-	рF
V _{I(cm)}	common-mode input voltage	$V_{INP} = V_{INM}$	0.9	1.5	2	V
B _i	input bandwidth		-	600	-	МН
$V_{I(dif)}$	differential input voltage	peak-to-peak	1		2	V
Common	mode output voltage: pin VCM					
V _{O(cm)}	common-mode output voltage		-	$V_{DDA}/2$	-	V
I _{O(cm)}	common-mode output current		-	<tbd></tbd>	-	μΑ
I/O refere	nce voltage: pin VREF					
V_{VREF}	voltage on pin VREF	output	0.5	-	1	V
		input	0.5	-	1	V
Accuracy						
INL	integral non-linearity		-0.4	±0.07	+0.4	LSE
DNL	differential non-linearity	guaranteed no missing codes	-0.06	±0.04	+0.06	LSE
E _{offset}	offset error		-	±2	-	mV
E _G	gain error	full-scale		±0.5		%
Supply						
PSRR	power supply rejection ratio	100 mV (p-p) on V _{DDA}	-	35	-	dBo

^[1] Typical values measured at $V_{DDA} = 3$ V, $V_{DDO} = 1.8$ V, $T_{amb} = 25$ °C and $C_L = 5$ pF; minimum and maximum values are across the full temperature range $T_{amb} = -40$ °C to +85 °C at $V_{DDA} = 3$ V, $V_{DDO} = 1.8$ V; $V_{INP} - V_{INM} = -1$ dBFS; internal reference mode; applied to CMOS and LVDS interface; unless otherwise specified.

10. Dynamic characteristics

10.1 Dynamic characteristics

Table 7. Dynamic characteristics[1]

Symbol	Parameter	Conditions	Al	DC1010S	6065	ΑC	C1010S	080	ΑI	DC1010S	105	AD	C1010S	125	Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Analog s	signal processi	ng	'	'	'		'	'	'	'	'	•	'	'	'
^Д 2Н	second	$f_i = 3 \text{ MHz}$	-	87	-	-	87	-	-	86	-	-	88	-	dBc
	harmonic level	$f_i = 30 \text{ MHz}$	-	86	-	-	86	-	-	86	-	-	87	-	dBc
	ievei	$f_i = 70 \text{ MHz}$	-	85	-	-	85	-	-	84	-	-	85	-	dBc
		f _i = 170 MHz	-	82	-	-	82	-	-	81	-	-	83	-	dBc
αзн	third	$f_i = 3 \text{ MHz}$	-	86	-	-	86	-	-	85	-	-	87	-	dBc
	harmonic level	$f_i = 30 \text{ MHz}$	-	85	-	-	85	-	-	85	-	-	86	-	dBc
	level	$f_i = 70 \text{ MHz}$	-	84	-	-	84	-	-	83	-	-	84	-	dBc
		f _i = 170 MHz	-	81	-	-	81	-	-	80	-	-	82	-	dBc
THD	total	f _i = 3 MHz	-	85	-	-	85	-	-	84	-	-	86	-	dBc
	harmonic distortion	$f_i = 30 \text{ MHz}$	-	84	-	-	84	-	-	84	-	-	85	-	dBc
	distortion	$f_i = 70 \text{ MHz}$	-	83	-	-	83	-	-	82	-	-	83	-	dBc
		$f_i = 170 \text{ MHz}$	-	80	-	-	80	-	-	79	-	-	81	-	dBc
ENOB	effective	f _i = 3 MHz	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
	number of bits	$f_i = 30 \text{ MHz}$	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
	DIIS	$f_i = 70 \text{ MHz}$	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
		$f_i = 170 \text{ MHz}$	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
SNR	signal-to-nois	f _i = 3 MHz	-	61.7	-	-	61.7	-	-	61.6	-	-	61.6	-	dBF
	e ratio	$f_i = 30 \text{ MHz}$	-	61.6	-	-	61.6	-	-	61.6	-	-	61.6	-	dBF:
		$f_i = 70 \text{ MHz}$	-	61.6	-	-	61.6	-	-	61.5	-	-	61.5	-	dBF:
		$f_i = 170 \text{ MHz}$	-	61.5	-	-	61.5	-	-	61.5	-	-	61.5	-	dBF
SFDR	spurious-free	$f_i = 3 \text{ MHz}$	-	86	-	-	86	-	-	85	-	-	87	-	dBc
	dynamic	$f_i = 30 \text{ MHz}$	-	85	-	-	85	-	-	85	-	-	86	-	dBc
	range	$f_i = 70 \text{ MHz}$	-	84	-	-	84	-	-	83	-	-	84	-	dBc
		f _i = 170 MHz	-	81	-	-	81	-	-	80	-	-	82	-	dBc

Symbol	Parameter	Conditions	Αľ	ADC1010S065			ADC1010S080			C1010S	105	AD	ADC1010S125		
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
IMD	Intermodulati	$f_i = 3 \text{ MHz}$	-	89	-	-	89	-	-	88	-	-	89	-	dBc
	on distortion	$f_i = 30 \text{ MHz}$	-	88	-	-	88	-	-	88	-	-	88	-	dBc
		f _i = 70 MHz	-	87	-	-	87	-	-	86	-	-	86	-	dBc
		f _i = 170 MHz	-	84	-	-	85	-	-	83	-	-	84	-	dBc

Typical values measured at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$, $V_{amb} = 25 \text{ °C}$ and $C_L = 5 \text{ pF}$; minimum and maximum values are across the full temperature range $T_{amb} = -40 \text{ °C}$ to +85 °C at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$; $V_{INP} - V_{INM} = -1 \text{ dBFS}$; internal reference mode; applied to CMOS and LVDS interface; unless otherwise specified.

NXP

Semiconductors

10.2 Clock and digital output timing

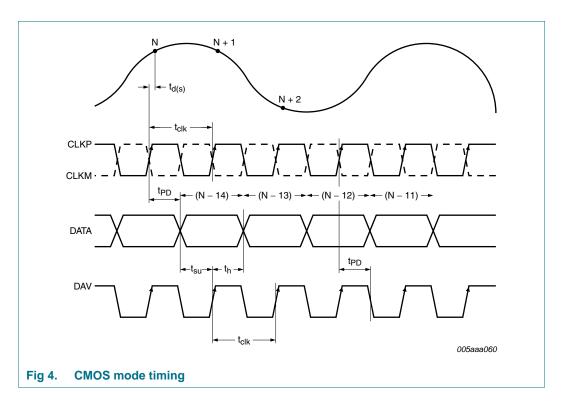
Table 8. Clock and digital output timing characteristics[1]

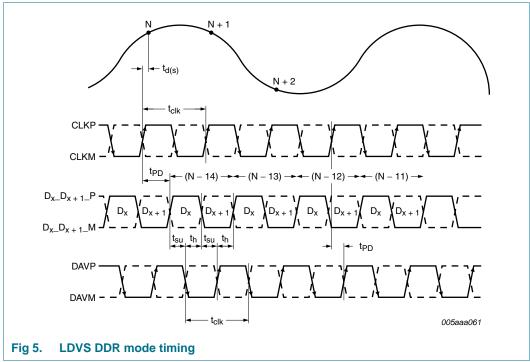
Clock duty cycle DCS_EN = 1 30 50 70 30	Symbol	Parameter	Conditions	ΑI	DC10105	8065	AI	C10105	080	AI	DC10105	105	ΑI	DC1010S	125	Unit
Clock frequency 20				Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Clock duty cycle DCS_EN = 1 30 50 70 30	Clock tir	ning input: pins (CLKP and CLKM			'			•		'	'	'	'	'	
time Clock duty cycle DCS_EN = 1 30 50 70 30 30 50 70 30 50 70 30 50 70 30 50 70 30 50 50 50 50 50 50 5	f _{clk}	clock frequency		20	-	65	60	-	80	75	-	105	100	-	125	MHz
DCS_EN = 0 45 50 55 45 50 55 45 50 55 45 50 55 45 50 55 %	t _{lat(data)}	•	clock cycles	-	14	-	-	14	-	-	14	-	-	14	-	clock cycle
Sampling delay time -	δ_{clk}	clock duty cycle	DCS_EN = 1	30	50	70	30	50	70	30	50	70	30	50	70	%
time wake-up time - < tbd> - <tbd> - - <tbr></tbr> - And the complex co</tbd></tbd></tbd></tbd></tbd>			DCS_EN = 0	45	50	55	45	50	55	45	50	55	45	50	55	%
DATA 0.5 -	t _{d(s)}			-	8.0	-	-	8.0	-	-	8.0	-	-	0.8	-	ns
Data	t _{wake}	wake-up time		-	<tbd></tbd>	-	-	<tbd></tbd>	-	-	<tbd></tbd>	-	-	<tbd></tbd>	-	ns
DAV -	CMOS m	node timing outpu	ıt: pins D9 to D0	and DAV												
set-up time	t _{PD}		DATA	-	3.9	-	-	3.9	-	-	3.9	-	-	3.9	-	ns
hold time rise time[2] DATA DAV DAV DATA DAV DATA DATA DATA DAT		delay	DAV	-	4.2	-	-	4.2	-	-	4.2	-	-	4.2	-	ns
rise time[2] DATA	t _{su}	set-up time		-	7.7	-	-	6.5	-	-	4.7	-	-	4.3	-	ns
DAV 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns fall time[2] DATA 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns VDS DDR mode timing output: pins D9P to D0P, D9M to D0M, DAVP and DAVM DDD propagation delay DATA - 3.9 3.9 3.9 3.9 3.9 - ns	t _h	hold time		-	6.7	-	-	5.5	-	-	3.8	-	-	3.5	-	ns
fall time 2 DATA 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns VDS DDR mode timing output: pins D9P to D0P, D9M to D0M, DAVP and DAVM DATA - 3.9 3.9 3.9 3.9 - ns delay DAV - 4.2 4.2 4.2 4.2 - ns su set-up time - 5.1 3.5 2.1 1.4 - ns hold time - 2.0 2.0 2.0 2.0 - ns rise time 3 DATA 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns DAV 0.5 - 2.4 ns	t _r	rise time[2]	DATA	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	ns
VDS DDR mode timing output: pins D9P to D0P, D9M to D0M, DAVP and DAVM PD			DAV	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	ns
PD propagation delay	t _f	fall time[2]	DATA	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	ns
DAV -	LVDS DE	OR mode timing o	output: pins D9P	to D0P, D	9M to D	OM, DAV	P and D	AVM								
set-up time 5.1 3.5 2.1 1.4 - ns hold time 2.0 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns DAV 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns	t _{PD}		DATA	-	3.9	-	-	3.9	-	-	3.9	-	-	3.9	-	ns
hold time - 2.0 2.0 2.0 2.0 2.0 - ns rise time DATA DAV 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns		delay	DAV	-	4.2	-	-	4.2	-	-	4.2	-	-	4.2	-	ns
rise time[3] DATA 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns DAV 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns	t _{su}	set-up time		+-	5.1	-	-	3.5	-	-	2.1	-	-	1.4	-	ns
DAV 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns	t _h	hold time		-	2.0	-	-	2.0	-	-	2.0	-	-	2.0	-	ns
	t _r	rise time[3]	DATA	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	ns
fall time[3] DATA 0.5 - 2.4 0.5 - 2.4 0.5 - 2.4 ns			DAV	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	ns
	t _f	fall time[3]	DATA	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	0.5	-	2.4	ns

^[1] Typical values measured at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$, $V_{amb} = 25 \text{ °C}$ and $C_L = 5 \text{ pF}$; minimum and maximum values are across the full temperature range $T_{amb} = -40 \text{ °C}$ to +85 °C at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$; $V_{INP} - V_{INM} = -1 \text{ dBFS}$; unless otherwise specified.

^[2] Measured between 20 % to 80 % of V_{DDO} .

^[3] Rise time measured from -50~mV to +50~mV; fall time measured from +50~mV to -50~mV.



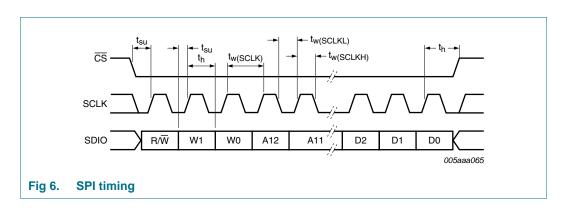


10.3 SPI timings

Table 9. SPI timings characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{w(SCLK)}$	SCLK pulse width		40	-	-	ns
t _{w(SCLKH)}	SCLK HIGH pulse width		16	-	-	ns
t _{w(SCLKL)}	SCLK LOW pulse width		16	-	-	ns
t _{su}	set-up time	data to SCLK HIGH	5	-	-	ns
		CS to SCLK HIGH	5	-	-	ns
t _h	hold time	data to SCLK HIGH	2	-	-	ns
		CS to SCLK HIGH	2	-	-	ns
f _{clk(max)}	maximum clock frequency		-	-	25	MHz

^[1] Typical values measured at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$, $T_{amb} = 25 ^{\circ}\text{C}$ and $C_L = 5 \text{ pF}$; minimum and maximum values are across the full temperature range $T_{amb} = -40 ^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$ at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$



11. Application information

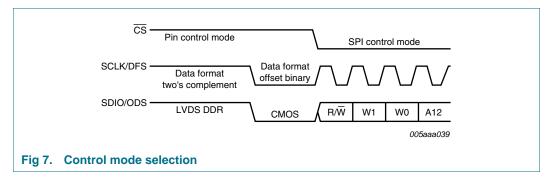
11.1 Device control

The ADC1010S can be controlled via SPI or directly via the I/O pins (PIN control mode).

11.1.1 SPI and Pin control modes

The device enters Pin control mode at power-up, and remains in this mode as long as pin CS is held HIGH. In Pin control mode, the SPI pins SDIO, CS and SCLK are used as static control pins.

SPI control mode is enabled by forcing pin $\overline{\text{CS}}$ LOW. Once SPI control mode has been enabled, the device will remain in this mode. The transition from Pin control mode to SPI control mode is illustrated in Figure 7.



When the device enters SPI control mode, the output data standard and data format are determined by the level on pin SDIO at the instant a transition is triggered by a falling edge on CS.

11.1.2 Operating mode selection

The active ADC1010S operating mode (Power-up, Power-down or Sleep) can be selected via the SPI interface (see <u>Table 20</u>) or using pins PWD and \overline{OE} in Pin control mode, as described in Table 10.

Table 10. Operating mode selection via pin PWD and OE

Pin PWD	Pin OE	Operating mode	Output high-Z
0	0	Power-up	no
0	1	Power-up	yes
1	0	Sleep	yes
1	1	Power-down	yes

11.1.3 Selecting the output data standard

The output data standard (CMOS or LVDS DDR) can be selected via the SPI interface (see <u>Table 23</u>) or using pin ODS in Pin control mode. LVDS DDR is selected when ODS is HIGH, otherwise CMOS is selected.

11.1.4 Selecting the output data format

The output data format can be selected via the SPI interface (offset binary, two's complement or gray code; see <u>Table 23</u>) or using pin DFS in Pin control mode (offset binary or two's complement). Offset binary is selected when DFS is LOW. When DFS is HIGH, two's complement is selected.

11.2 Analog inputs

11.2.1 Input stage

The analog input of the ADC1010S supports differential or single-ended input drive. Optimal performance is achieved using differential inputs with the common-mode input voltage ($V_{I(cm)}$) on pins INP and INM set to 0.5 V_{DDA} .

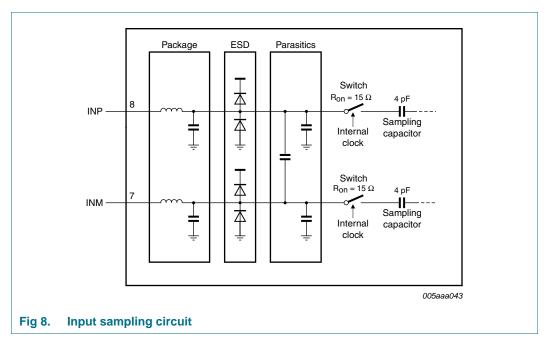
The full-scale analog input voltage range is configurable between 1 V (p-p) and 2 V (p-p) via a programmable internal reference (see Section 11.3 and Table 22 further details).

The equivalent circuit of the sample and hold input stage, including Electrostatic Discharge (ESD) protection and circuit and package parasitics, is shown in <u>Figure 8</u>.

ADC1010S_SER_1

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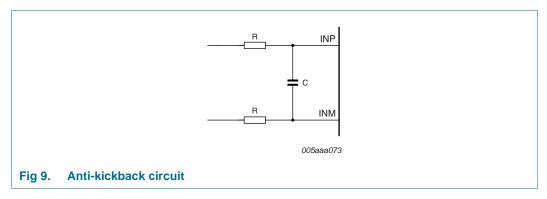


The sample phase occurs when the internal clock (derived from the clock signal on pin CLKP/CLKM) is HIGH. The voltage is then held on the sampling capacitors. When the clock signal goes LOW, the stage enters the hold phase and the voltage information is transmitted to the ADC core.

11.2.2 Anti-kickback circuitry

Anti-kickback circuitry (R-C filter in <u>Figure 9</u>) is needed to counteract the effects of a charge injection generated by the sampling capacitance.

The RC filter is also used to filter noise from the signal before it reaches the sampling stage. The value of the capacitor should be chosen to maximize noise attenuation without degrading the settling time excessively.



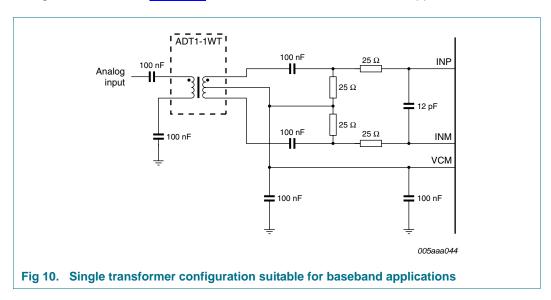
The component values are determined by the input frequency and should be selected so as not to affect the input bandwidth.

Table 11. RC coupling versus input frequency - typical values

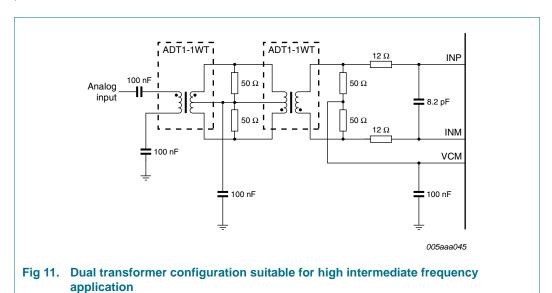
Input frequency	R	С
3 MHz	25 Ω	12 pF
70 MHz	12 Ω	8 pF
170 MHz	12 Ω	8 pF

11.2.3 Transformer

The configuration of the transformer circuit is determined by the input frequency. The configuration shown in Figure 10 would be suitable for a baseband application.



The configuration shown in <u>Figure 11</u> is recommended for high frequency applications. In both cases, the choice of transformer will be a compromise between cost and performance.

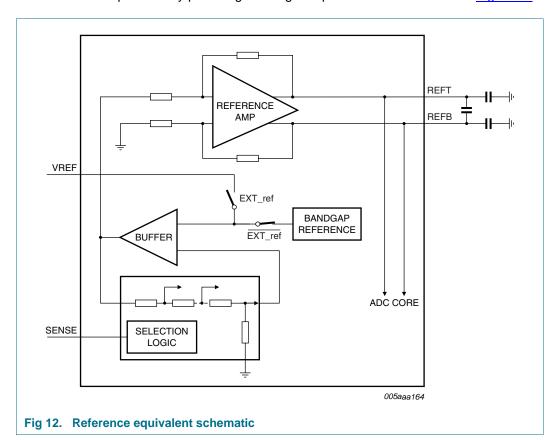


ADC1010S_SER_1

11.3 System reference and power management

11.3.1 Internal/external references

The ADC1010S has a stable and accurate built-in internal reference voltage to adjust the ADC full-scale. This reference voltage can be set internally via SPI or with pins VREF and SENSE (programmable in 1 dB steps between 0 dB and –6 dB via control bits INTREF[2:0] when bit INTREF_EN = 1; see <u>Table 22</u>). See <u>Figure 13</u>, <u>Figure 14</u>, <u>Figure 15</u> and <u>Figure 16</u>. The equivalent reference circuit is shown in <u>Figure 12</u>. External reference is also possible by providing a voltage on pin VREF as described in Figure 15.



If bit INTREF_EN is set to 0, the reference voltage will be determined either internally or externally as detailed in <u>Table 12</u>.

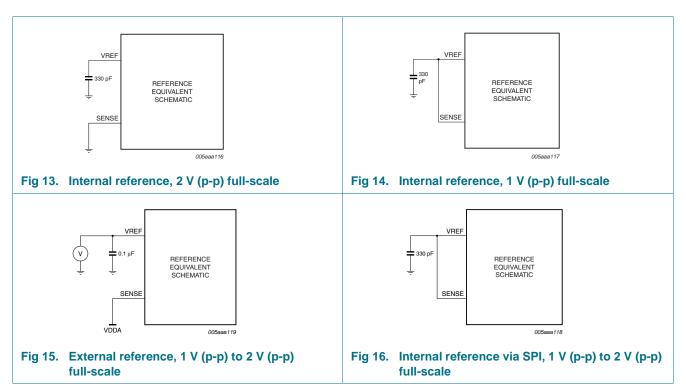
Table 12. Reference selection

Selection	SPI bit INTREF_EN	SENSE pin	VREF pin	full-scale (p-p)
internal (Figure 13)	0	AGND	330 pF capacitor to AGND	2 V
internal (Figure 14)	0	pin VREF connected to pin SENSE and via 1 V a 330 pF capacitor to AGND		
external (Figure 15)	0	V_{DDA}	external voltage between 0.5 V and 1 V[1]	1 V to 2 V
internal via SPI (Figure 16)	1	pin VREF connected to pin SENSE and via 1 V to 2 V 330 pF capacitor to AGND		

^[1] The voltage on pin VREF is doubled internally to generate the internal reference voltage.

ADC1010S_SER_1

<u>Figure 13</u> to <u>Figure 16</u> illustrate how to connect the SENSE and VREF pins to select the required reference voltage source.



11.3.2 Reference gain control

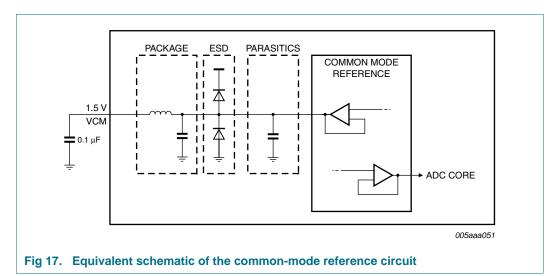
The reference gain is programmable between 0 dB to -6 dB in 1 dB steps via the SPI (see <u>Table 22</u>). The corresponding full-scale input voltage range varies between 2 V (p-p) and 1 V (p-p), as shown in <u>Table 13</u>:

Table 13. Reference SPI gain control

INTREF[2:0]	Gain (dB)	Full-scale (V (p-p))
000	0 dB	2 V
001	−1 dB	1.78 V
010	−2 dB	1.59 V
011	−3 dB	1.42 V
100	−4 dB	1.26 V
101	−5 dB	1.12 V
110	−6 dB	1 V
111	reserved	х

11.3.3 Common-mode output voltage (V_{O(cm)})

A 0.1 μ F filter capacitor should be connected between pin VCM and ground to ensure a low-noise common-mode output voltage. When AC-coupled, pin VCM can then be used to set the common-mode reference for the analog inputs, for instance via a transformer middle point.



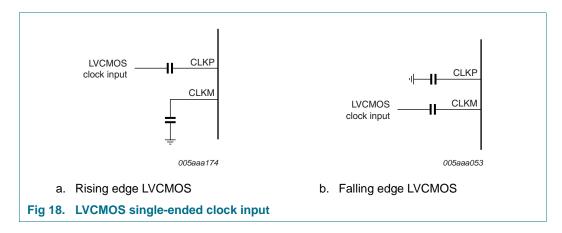
11.3.4 Biasing

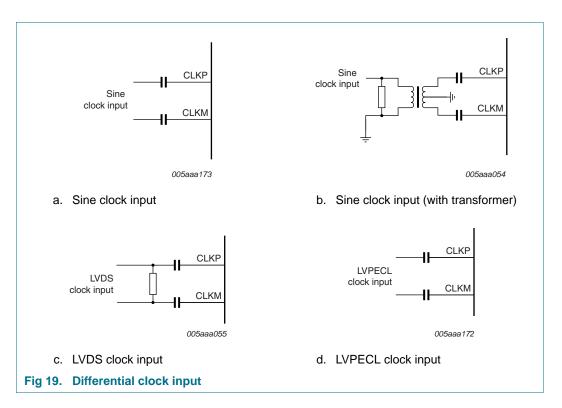
The common-mode input voltage ($V_{I(cm)}$) on pins INP and INM should be set externally to 0.5 V_{DDA} for optimal performance and should always be between 0.9 V and 2 V.

11.4 Clock input

11.4.1 Drive modes

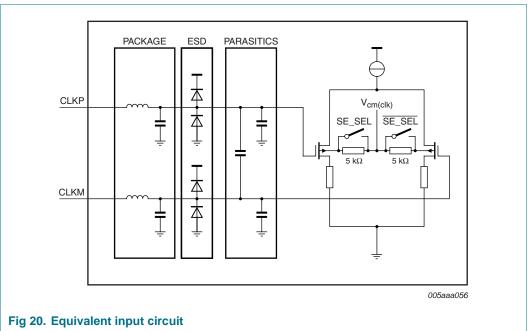
The ADC1010S can be driven differentially (SINE, LVPECL or LVDS) with little or no influence on the dynamic performances. It can also be driven by a single-ended LVCMOS signal connected to pin CLKP (CLKM should be connected to ground via a capacitor) or CLKM (CLKP should be connected to ground via a capacitor).





11.4.2 Equivalent input circuit

The equivalent circuit of the input clock buffer is shown in Figure 20. The common-mode voltage of the differential input stage is set via internal 5 k Ω resistors.



Single-ended or differential clock inputs can be selected via the SPI interface (see <u>Table 21</u>). If single-ended is enabled, the input pin (CLKM or CLKP) is selected via control bit SE_SEL.

If single-ended is implemented without setting SE_SEL to the appropriate value, the unused pin should be connected to ground via a capacitor.

11.4.3 Duty cycle stabilizer

The duty cycle stabilizer can improve the overall performances of the ADC by compensating the duty cycle of the input clock signal. When the duty cycle stabilizer is active (bit DCS_EN = 1; see $\underline{\text{Table 21}}$), the circuit can handle signals with duty cycles of between 30 % and 70 % (typical). When the duty cycle stabilizer is disabled (DCS_EN = 0), the input clock signal should have a duty cycle of between 45 % and 55 %.

11.4.4 Clock input divider

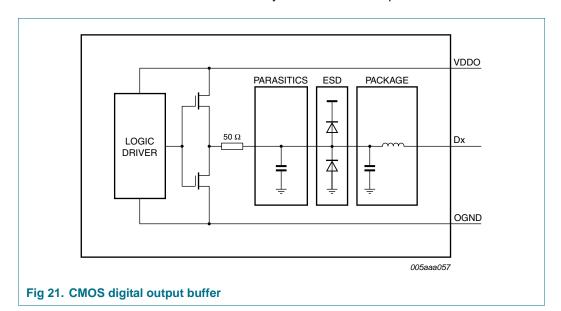
The ADC1010S contains an input clock divider that divides the incoming clock by a factor of 2 (when bit CLKDIV = 1; see <u>Table 21</u>). This feature allows the user to deliver a higher clock frequency with better jitter performance, leading to a better SNR result once acquisition has been performed.

11.5 Digital outputs

11.5.1 Digital output buffers: CMOS mode

The digital output buffers can be configured as CMOS by setting bit LVDS/CMOS to 0 (see Table 23).

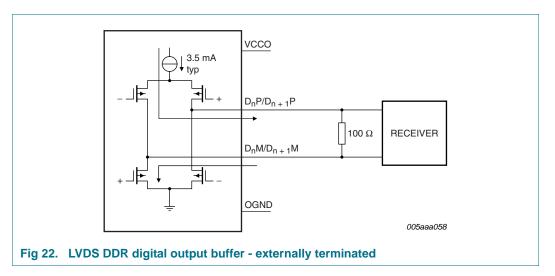
Each digital output has a dedicated output buffer. The equivalent circuit of the CMOS digital output buffer is shown in Figure 21. The buffer is powered by a separate power supply, pins OGND and V_{DDO} , to ensure 1.8 V to 3.3 V compatibility and is isolated from the ADC core. Each buffer can be loaded by a maximum of 10 pF.



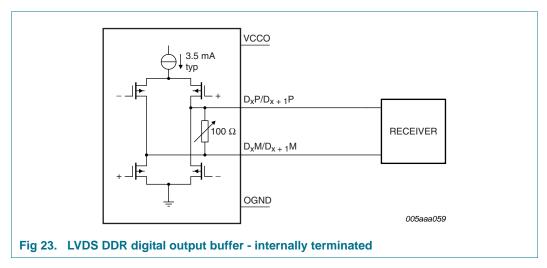
The output resistance is 50 Ω and is the combination of the an internal resistor and the equivalent output resistance of the buffer. There is no need for an external damping resistor. The drive strength of both data and DAV buffers can be programmed via the SPI in order to adjust the rise and fall times of the output digital signals (see <u>Table 30</u>):

11.5.2 Digital output buffers: LVDS DDR mode

The digital output buffers can be configured as LVDS DDR by setting bit LVDS/CMOS to 1 (see Table 23).



Each output should be terminated externally with a 100 Ω resistor (typical) at the receiver side (<u>Figure 22</u>) or internally via SPI control bits LVDS_INT_TER[2:0] (see <u>Figure 23</u> and Table 32).



The default LVDS DDR output buffer current is set to 3.5 mA. It can be programmed via the SPI (bits DAVI[1:0] and DATA[1:0]; see <u>Table 31</u>) in order to adjust the output logic voltage levels.

Table 14. LVDS DDR output register 2

LVDS_INT_TER[2:0]	Resistor value (Ω)
000	no internal termination
001	300
010	180
011	110
100	150
101	100
110	81
111	60

11.5.3 Data valid (DAV) output clock

A data valid output clock signal (DAV) can be used to capture the data delivered by the ADC1010S. Detailed timing diagrams for CMOS and LVDS DDR modes are shown in Figure 4 and Figure 5 respectively.

11.5.4 Out-of-Range (OTR)

An out-of-range signal is provided on pin OTR. The latency of OTR is fourteen clock cycles. The OTR response can be speeded up by enabling Fast OTR (bit FASTOTR = 1; see <u>Table 29</u>). In this mode, the latency of OTR is reduced to only four clock cycles. The Fast OTR detection threshold (below full-scale) can be programmed via bits FASTOTR_DET[2:0].

Table 15. Fast OTR register

FASTOTR_DET[2:0]	Detection level (dB)
000	-20.56
001	-16.12
010	-11.02
011	-7.82
100	-5.49
101	-3.66
110	-2.14
111	-0.86

11.5.5 Digital offset

By default, the ADC1010S delivers output code that corresponds to the analog input. However it is possible to add a digital offset to the output code via the SPI (bits DIG_OFFSET[5:0]; see Table 25).

11.5.6 Test patterns

For test purposes, the ADC1010S can be configured to transmit one of a number of predefined test patterns (via bits TESTPAT_SEL[2:0]; see <u>Table 26</u>). A custom test pattern can be defined by the user (TESTPAT_USER; see <u>Table 27</u> and <u>Table 28</u>) and is selected when TESTPAT_SEL[2:0] = 101. The selected test pattern will be transmitted regardless of the analog input.

11.5.7 Output codes versus input voltage

Table 16. Output codes

$V_{INP} - V_{INM}$	Offset binary	Two's complement	OTR pin
< -1	00 0000 0000	10 0000 0000	1
-1.0000000	00 0000 0000	10 0000 0000	0
-0.9980469	00 0000 0001	10 0000 0001	0
-0.9960938	00 0000 0010	10 0000 0010	0
-0.9941406	00 0000 0011	10 0000 0011	0
-0.9921875	00 0000 0100	10 0000 0100	0
			0
-0.0039063	01 1111 1110	11 1111 1110	0
-0.0019531	01 111 1111	11 1111 1111	0
0.0000000	10 0000 0000	00 0000 0000	0
+0.0019531	10 0000 0001	00 0000 0001	0
+0.0039063	10 0000 0010	00 0000 0010	0
			0
+0.9921875	11 1111 1011	01 1111 1011	0
+0.9941406	11 1111 1100	01 1111 1100	0
+0.9960938	11 1111 1101	01 1111 1101	0
+0.9980469	11 1111 1110	01 1111 1110	0
+1.0000000	11 1111 1111	01 1111 1111	0
> +1	11 1111 1111	01 1111 1111	1

11.6 Serial peripheral interface

11.6.1 Register description

The ADC1010S serial interface is a synchronous serial communications port that allows for easy interfacing with many commonly-used microprocessors. It provides access to the registers that control the operation of the chip.

This interface is configured as a 3-wire type (SDIO as bidirectional pin)

Pin SCLK is the serial clock input and \overline{CS} is the chip select pin.

Each read/write operation is initiated by a LOW level on \overline{CS} . A minimum of three bytes will be transmitted (two instruction bytes and at least one data byte). The number of data bytes is determined by the value of bits W1 and W2 (see Table 18).

Table 17. Instruction bytes for the SPI

	MSB							LSB
Bit	7	6	5	4	3	2	1	0
Description	R/W[1]	W1[2]	W0[2]	A12	A11	A10	A9	A8
	A7	A6	A5	A4	А3	A2	A1	A0

^[1] Bit R/\overline{W} indicates whether it is a read (1) or a write (0) operation.

ADC1010S_SER_1

^[2] Bits W1 and W0 indicate the number of bytes to be transferred after the instruction byte (see Table 18).

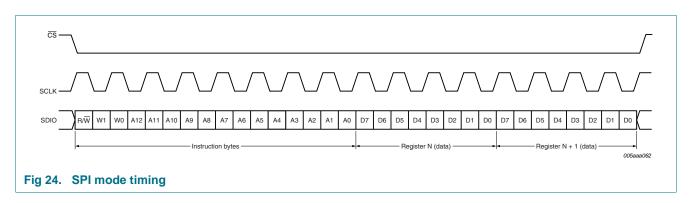
Table 18. Number of data bytes to be transferred after the instruction bytes

W1	W0	Number of bytes transmitted
0	0	1 byte
0	1	2 bytes
1	0	3 bytes
1	1	4 bytes or more

Bits A12 to A0 indicate the address of the register being accessed. In the case of a multiple byte transfer, this address is the first register to be accessed. An address counter is increased to access subsequent addresses.

The steps involved in a data transfer are as follows:

- 1. A falling edge on $\overline{\text{CS}}$ in combination with a rising edge on SCLK determine the start of communications.
- 2. The first phase is the transfer of the 2-byte instruction.
- 3. The second phase is the transfer of the data which can vary in length but will always be a multiple of 8 bits. The MSB is always sent first (for instruction and data bytes).
- 4. A rising edge on $\overline{\text{CS}}$ indicates the end on data transmission.

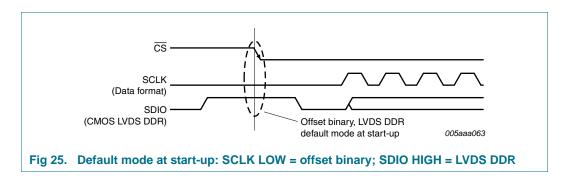


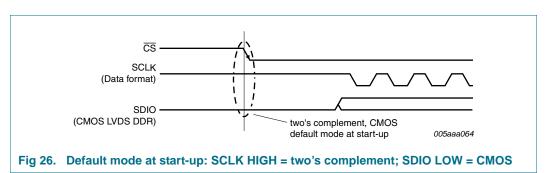
11.6.2 Default modes at start-up

During circuit initialization, it does not matter which output data standard has been selected. At power-up, the device enters Pin control mode.

A falling edge on $\overline{\text{CS}}$ will trigger a transition to SPI control mode. When the ADC1010S enters SPI control mode, the output data standard (CMOS/LVDS DDR) is determined by the level on pin SDIO (see <u>Figure 25</u>). Once in SPI control mode, the output data standard can be changed via bit LVDS/CMOS in <u>Table 23</u>.

When the ADC1010S enters SPI control mode, the output data format (two's complement or offset binary) is determined by the level on pin SCLK (gray code can only be selected via the SPI). Once in SPI control mode, the output data format can be changed via bit DATA_FORMAT[1:0] in <u>Table 23</u>.





Preliminary data sheet

11.6.3 Register allocation map

Table 19. Register allocation map

AddrHex	Register name	R/W	Bit definition								Defaul
			Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Bin
0005	Reset and operating mode	R/W	SW_RST		RESERVED	[2:0]	-	-	OP_MC	DE[1:0]	0000 0000
0006	Clock	R/W	-	-	-	SE_SEL	DIFF_SE	-	CLKDIV	DCS_EN	0000 0001
8000	Internal reference	R/W	-	-	-	-	INTREF_EN		INTREF[2:0]		0000 0000
0011	Output data standard	R/W	-	-	-	LVDS_ CMOS	OUTBUF	OUTBUS_ SWAP	DATA_FO	RMAT[1:0]	0000 0000
0012	Output clock	R/W	-	-	-	-	DAVINV	D/	AVPHASE[2:0]		0000 1110
0013	Offset	R/W	-	- DIG_OFFSET[5:0]				0000			
0014	Test pattern 1	R/W	-	-	-	-	-	TES	STPAT_SEL[2:	0]	0000
0015	Test pattern 2	R/W				TES	STPAT_USER[9:2]				0000
0016	Test pattern 3	R/W	TESTPA USER[1:				-	-	-	-	0000 0000
0017	Fast OTR	R/W	-	-	-	-	FASTOTR	FAS	TOTR_DET[2	:0]	0000
0020	CMOS output	R/W	-	-	-	-	DAV_DRV[1:0] DATA_DRV[1:0]		DRV[1:0]	0000 1110	
0021	LVDS DDR O/P 1	R/W	-	-	DAVI_x2_EN	I	DAVI[1:0]	DATAI_ x2_EN	DATA	AI[1:0]	0000 0000
0022	LVDS DDR O/P 2	R/W	-	-	-	-	BIT_BYTE_WISE	LVD	S_INT_TER[2	:0]	0000 0000

Table 20. Reset and operating mode control register (address 0005h) bit description

Bit	Symbol	Access	Value	Description
7	SW_RST	R/W		reset digital section
			0	no reset
			1	performs a reset on SPI registers
6 to 4	RESERVED[2:0]		000	reserved
3 to 2	-		00	not used
1 to 0	OP_MODE[1:0]	R/W		operating mode
			00	normal (power-up)
			01	power-down
		10	sleep	
			11	normal (power-up)

Table 21. Clock control register (address 0006h) bit description

		3 (-	,	The state of the s
Bit	Symbol	Access	Value	Description
7 to 5	-		000	not used
4	SE_SEL	R/W		single-ended clock input pin select
			0	CLKM
			1	CLKP
3	DIFF_SE	R/W		differential/single ended clock input select
			0	fully differential
			1	single-ended
2	-		0	not used
1	CLKDIV	R/W		clock input divide by 2
			0	disabled
			1	enabled
0	DCS_EN	R/W		duty cycle stabilizer
			0	disabled
			1	enabled

Table 22. Internal reference control register (address 0008h) bit description

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	INTREF_EN	R/W		programmable internal reference enable
			0	disable
			1	active
2 to 0	INTREF[2:0]	R/W		programmable internal reference
			000	0 dB (FS = 2 V)
			001	−1 dB (FS = 1.78 V)
			010	−2 dB (FS = 1.59 V)
		011	011	−3 dB (FS = 1.42 V)
			100	−4 dB (FS = 1.26 V)
			101	−5 dB (FS = 1.12 V)
			110	−6 dB (FS = 1 V)
			111	reserved

Table 23. Output data standard control register (address 0011h) bit description

Bit	Symbol	Access	Value	Description
7 to 5	-		000	not used
4	LVDS_CMOS	R/W		output data standard: LVDS DDR or CMOS
			0	CMOS
			1	LVDS DDR
3	OUTBUF	R/W		output buffers enable
			0	output enabled
		1	output disabled (high Z)	
2	OUTBUS_SWAP	R/W		output bus swapping
			0	no swapping
			1	output bus is swapping (MSB becomes LSB and vice versa)
1 to 0	DATA_FORMAT[1:0]	R/W		output data format
			00	offset binary
			01	two's complement
			10	gray code
			11	offset binary

Table 24. Output clock register (address 0012h) bit description

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	DAVINV	R/W		output clock data valid (DAV) polarity
			0	normal
			1	inverted
2 to 0	DAVPHASE[2:0]	R/W		DAV phase select
			000	output clock shifted (ahead) by 3 ns
			001	output clock shifted (ahead) by 2.5 ns
			010	output clock shifted (ahead) by 2 ns
			011	output clock shifted (ahead) by 1.5 ns
			100	output clock shifted (ahead) by 1 ns
			101	output clock shifted (ahead) by 0.5 ns
			110	default value as defined in timing section
			111	output clock shifted (delayed) by 0.5 ns

Table 25. Offset register (address 0013h) bit description

Bit	Symbol	Access	Value	Description
7 to 6	-		00	not used
5 to 0 DIG_OFFSET[5:0] R/W	R/W		digital offset adjustment	
		011111	+31 LSB	
			000000	0
			100000	–32 LSB

Table 26. Test pattern register 1 (address 0014h) bit description

		•		
Bit	Symbol	Access	Value	Description
7 to 3	-		00000	not used
2 to 0	TESTPAT_SEL[2:0]	R/W		digital test pattern select
			000	off
			001	mid scale
			010	-FS
			011	+FS
			100	toggle '11111111'/'00000000'
			101	custom test pattern
			110	'10101010.'
			111	'0101010'
			111	'0101010'

Table 27. Test pattern register 2 (address 0015h) bit description

Bit	Symbol	Access	Value	Description
7 to 0	TESTPAT_USER[9:2]	R/W	00000000	custom digital test pattern (bits 9 to 2)

Table 28. Test pattern register 3 (address 0016h) bit description

Bit	Symbol	Access	Value	Description
7 to 6	TESTPAT_USER[1:0]	R/W	00	custom digital test pattern (bits 1 to 0)
5 to 0	-		000000	not used

Table 29. Fast OTR register (address 0017h) bit description

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	FASTOTR	R/W		fast Out-of-Range (OTR) detection
			0	disabled
			1	enabled
2 to 0	FASTOTR_DET[2:0]	R/W		set fast OTR detect level
			000	-20.56 dB
			001	–16.12 dB
			010	–11.02 dB
			011	−7.82 dB
			100	−5.49 dB
			101	−3.66 dB
			110	−2.14 dB
			111	−0.86 dB

Table 30. CMOS output register (address 0020h) bit description

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3 to 2	DAV_DRV[1:0]	R/W		drive strength for DAV CMOS output buffer
	00	low		
			01	medium
			10	high
			11	very high
1 to 0	DATA_DRV[1:0]	R/W		drive strength for DATA CMOS output buffer
			00	low
			01	medium
			10	high
			11	very high

Table 31. LVDS DDR output register 1 (address 0021h) bit description

Symbol	Accoss	Value	Description
Syllibol	ACCESS		•
-		00	not used
DAVI_x2_EN	R/W		double LVDS current for DAV LVDS buffer
		0	disabled
		1	enabled
DAVI[1:0]	R/W		LVDS current for DAV LVDS buffer
		00	3.5 mA
		01	4.5 mA
		10	1.25 mA
		11	2.5 mA
DATAI_x2_EN	R/W		double LVDS current for DATA LVDS buffer
		0	disabled
		1	enabled
DATAI[1:0]	R/W		LVDS current for DATA LVDS buffer
		00	3.5 mA
		01	4.5 mA
		10	1.25 mA
		11	2.5 mA
	DAVI_x2_EN DAVI[1:0] DATAI_x2_EN	DAVI_x2_EN R/W DAVI[1:0] R/W DATAI_x2_EN R/W	- 00 DAVI_x2_EN R/W 0 1 DAVI[1:0] R/W 00 01 10 11 DATAI_x2_EN R/W 0 1 DATAI[1:0] R/W 0 1 DATAI[1:0] R/W

Table 32. LVDS DDR output register 2 (address 0022h) bit description

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	BIT_BYTE_WISE	R/W		DDR mode for LVDS output
			0	bit wise (even data bits output on DAV rising edge/odd data bits output on DAV falling edge)
			1	byte wise (MSB data bits output on DAV rising edge/LSB data bits output on DAV falling edge)
2 to 0	LVDS_INTTER[2:0]	R/W		internal termination for LVDS buffer (DAV and DATA)
			000	no internal termination
			001	300 Ω
			010	180 Ω
			011	110 Ω
			100	150 Ω
			101	100 Ω
			110	81 Ω
			111	60 Ω

12. Package outline

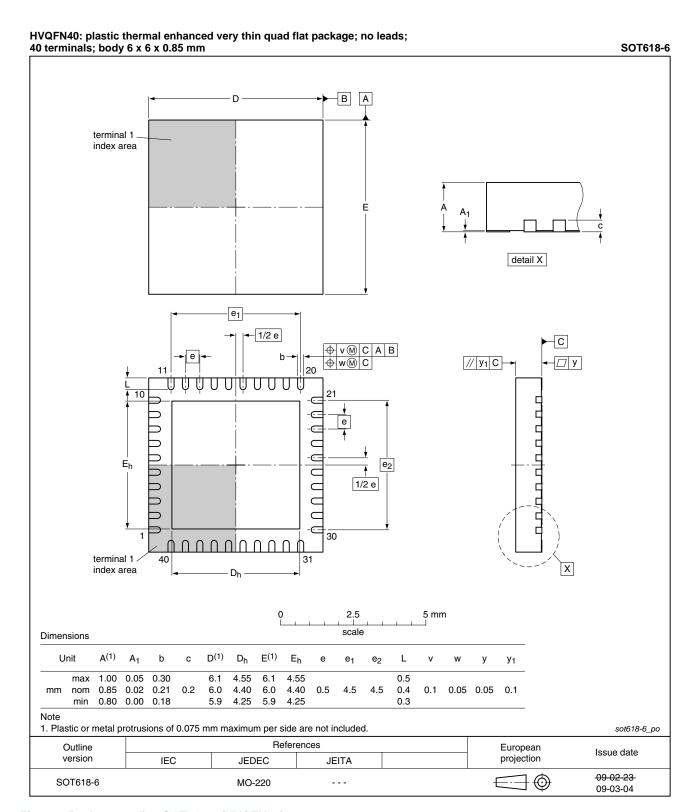


Fig 27. Package outline SOT618-6 (HVQFN40)

ADC1010S_SER_1

13. Revision history

Table 33. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ADC1010S_SER_1	20100409	Preliminary data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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ADC1010S_SER_1

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ADC1010S series

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16. Contents

1	General description	
2	Features and benefits	
3	Applications	
_		
4	Ordering information	
5	Block diagram 2	
6	Pinning information 3	
6.1	Pinning	,
6.2	Pin description	,
7	Limiting values 5	,
8	Thermal characteristics 5	,
9	Static characteristics 6	;
10	Dynamic characteristics	}
10.1	Dynamic characteristics	
10.1	Clock and digital output timing	
10.3	SPI timings	
11	Application information	
11.1	Device control	
11.1.1	SPI and Pin control modes	
11.1.2	Operating mode selection	
11.1.3	Selecting the output data standard	
11.1.4	Selecting the output data format	
11.2	Analog inputs	
11.2.1	Input stage	
11.2.2	Anti-kickback circuitry	
11.2.3	Transformer	,
11.3	System reference and power management 16	í
11.3.1	Internal/external references 16	i
11.3.2	Reference gain control	
11.3.3	Common-mode output voltage (V _{O(cm)}) 18	,
11.3.4	Biasing	,
11.4	Clock input	,
11.4.1	Drive modes	,
11.4.2	Equivalent input circuit	
11.4.3	Duty cycle stabilizer 20	
11.4.4	Clock input divider 20	
11.5	Digital outputs	
11.5.1	Digital output buffers: CMOS mode 20	
11.5.2	Digital output buffers: LVDS DDR mode 21	
11.5.3	Data valid (DAV) output clock	
11.5.4	Out-of-Range (OTR)	
11.5.5	Digital offset	
11.5.6	Test patterns	
11.5.7	Output codes versus input voltage 23	
11.6	Serial peripheral interface	
11.6.1	Register description 23	
11.6.2	Default modes at start-up 24	

11.6.3	Register allocation map	26
12	Package outline	32
13	Revision history	33
14	Legal information	34
14.1	Data sheet status	34
14.2	Definitions	34
14.3	Disclaimers	34
14.4	Trademarks	35
15	Contact information	35
16	Contents	36

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